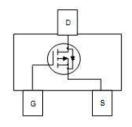
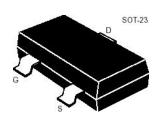


SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)





P-Channel Enhancement-Mode MOS FETs

P 沟道增强型 MOS 场效应管

■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	$\mathrm{BV}_{\mathrm{DSS}}$	-20	V
Gate- Source Voltage 栅極-源極電壓	$ m V_{GS}$	<u>±</u> 10	V
Drain Current (continuous) 漏極電流-連續	I_{D}	-2.2	A
Drain Current (pulsed) 漏極電流-脉冲	${ m I}_{ m DM}$	-8	A
Total Device Dissipation 總耗散功率 TA=25℃環境溫度爲 25℃	P_{D}	700	mW
Junction 結溫	$T_{\mathtt{J}}$	150	°C
Storage Temperature 儲存溫度	$T_{ m stg}$	-55to+150	°C

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■ELECTRICAL CHARACTERISTICS 電特性

(T_A=25℃ unless otherwise noted 如無特殊說明,溫度爲 25℃)

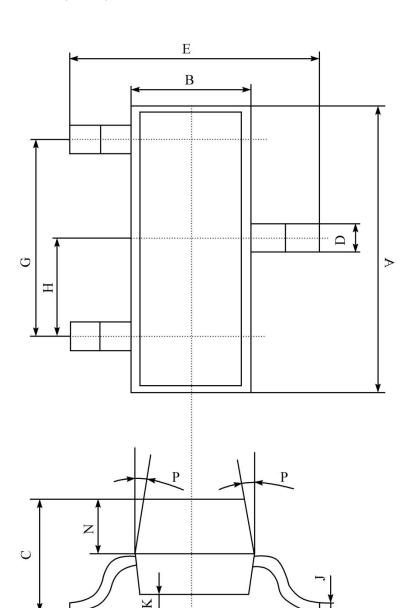
Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓(I _D = -250uA,V _{GS} =0V)	BV _{DSS}	-20	_	_	V
Gate Threshold Voltage 栅極開启電壓(ID= -250uA,VGS= VDS)	V _{GS(th)}	-0.4	-0.62	-1.5	V
Diode Forward Voltage Drop 内附二極管正向壓降(Is= -0.75A,VGS=0V)	V_{SD}			-1.5	V
Zero Gate Voltage Drain Current 零栅壓漏極電流(VGS=0V, VDS= -16V) (VGS=0V, VDS= -16V, TA=55°C)	I _{DSS}	_		-1 -10	uA
Gate Body Leakage 栅極漏電流(VGS= <u>+</u> 8V, VDS=0V)	IGSS	_	_	<u>±</u> 100	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻(I _D = -1.5A,VGS= -4.5V)	R _{DS(ON)}		90	120	mΩ
Static Drain-Source On-State Resistance 静态漏源導通電阻(I _D = -1.5A,V _{GS} = -2.5V)	R _{DS(ON)}	_	115	150	m Ω
Input Capacitance 輸入電容 (VGS=0V, VDS= -10V,f=1MHz)	Ciss	_	200	_	pF
Output Capacitance 輸出電容 (VGS=0V, VDS= -10V,f=1MHz)	Coss	_	80	_	pF
Turn-ON Time 开启時間 (V _{DS} = -10V, I _D = -2.7A, R _{GEN} =6Ω)	t(on)		8		ns
Turn-OFF Time 关断時間 (V _{DS} = -10V, I _D = -2.7A, R _{GEN} =6Ω)	t(off)	_	60	_	ns

Pulse Width \leq 300 μ s; Duty Cycle \leq 2.0%

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■ **DIMENSION** 外形封裝尺寸 單位(UNIT): mm



序號	數值及公差
A	2.90 ± 0.10
В	1.30 ± 0.10
C	1.00 ± 0.10
D	0.40 ± 0.10
Е	2.40 ± 0.20
G	1.90 ± 0.10
Н	0.95 ± 0.05
J	0.13 ± 0.05
K	0.00-0.10
M	≥0.2
N	0.60 ± 0.10
P	7±2°

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